

EAST Search History

(20 pp) 

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1214	sputtering near4 ("SnO.sub.2" "ZnO")	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/11/23 13:11
L2	211	sputtering near4 ("SnO.sub.2" "ZnO") and channel and semiconductor	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/11/23 13:11
L3	4	sputtering near4 ("SnO.sub.2" "ZnO") and channel and semiconductor and (Carcia.in. Cillessen.in.)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/11/23 13:55
L4	1	("6,100,558").PN.	USPAT; USOCR	OR	OFF	2007/11/23 14:41
L5	13512	((257/49) or (257/52) or (257/55) or (257/56) or (257/57) or (257/58) or (257/59) or (257/62) or (257/63) or (257/72) or (257/200) or (257/201) or (257/213) or (257/288) or (257/390) or (257/403) or (257/406) or (257/410) or (257/411)).CCLS.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/11/23 14:42
L6	6	5 and (thin adj film adj transistor tft) and (zinc-tin-oxide Zn-Sn-oxide (ZnO near10 "SnO.sub.2") ("Zn.sub.2" near1 "SnO.sub.4") zinc adj stann?te "ZnSnO.sub.3") near20 channel	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/11/23 14:46
L7	3	((randy near2 hoffman).in. (hai near2 chiang).in. (john near2 wager).in. hewlett.as. oregon.as.) and (thin adj film adj transistor tft). clm. and (zinc-tin-oxide Zn-Sn-oxide (ZnO near10 "SnO.sub.2") ("Zn.sub.2" near1 "SnO.sub.4") zinc adj stann?te "ZnSnO.sub.3") near20 channel.clm.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/11/23 14:48

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S1	3	("5,470,768") or ("5,879,973") or ("6,569,720")).PN.	USPAT; EPO; JPO; IBM_TDB	OR	OFF	2006/05/31 15:33
S2	20	("20036013261") or ("6561174") or ("20030104659") or ("20030139026") or ("20030180996") or ("20030186489") or ("20030207502") or ("20030218221") or ("20030218222") or ("20030219530") or ("20030224550")).PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/01 16:48
S3	10	("20036013261") or ("6561174") or ("20030104659") or ("20030139026") or ("20030180996") or ("20030186489") or ("20030207502") or ("20030218221") or ("20030218222") or ("20030219530") or ("20030224550")).PN.	US-PGPUB; USPAT	OR	OFF	2005/10/01 16:53
S4	1	("20030013261").PN.	US-PGPUB; USPAT	OR	OFF	2005/10/01 16:52
S5	11	S3 S4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/01 16:53
S6	9	("4559238") or ("4589026") or ("4887255") or ("5107314") or ("5744864") or ("6255130") or ("6255655") or ("6362499") or ("6391462")).PN. or ((2002/0153587) or (2002/0171085)).CCLS.	US-PGPUB; USPAT	OR	OFF	2005/10/01 16:56
S7	11	("4559238") or ("4589026") or ("4887255") or ("5107314") or ("5744864") or ("6255130") or ("6255655") or ("6362499") or ("6391462") or ("20020153587") or ("20020171085")).PN.	US-PGPUB; USPAT	OR	OFF	2005/10/01 16:57
S8	0	ep-0040076\$-\$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/01 16:58

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S9	0	ep-00040076\$-\$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/01 16:59
S10	82	sasano.in.	EPO	OR	OFF	2005/10/01 17:02
S11	0	sasano.in. and drain and compound	EPO	OR	OFF	2005/10/01 17:01
S12	0	sasano.in. and drain	EPO	OR	OFF	2005/10/01 17:02
S13	4	sasano.in. and semiconductor	EPO	OR	OFF	2005/10/01 17:02
S14	1	(EP-40076-\$).did.	EPO	OR	OFF	2005/10/01 17:08
S15	4	((("5,744,864") or ("20020101557")). PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/01 17:08
S16	2	((("5,744,864") or ("20020101557")). PN.	US-PGPUB; USPAT	OR	OFF	2005/10/01 17:08
S17	4	"763353".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/05/31 11:40
S18	4	"763353".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/05/31 11:42
S19	2	"20040127038".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/05/31 11:51
S20	5	"2004023432".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/05/31 11:52
S21	2	"20040023432".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/05/31 11:53
S22	4	S19 S21	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/05/31 11:55

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S23	2	jp-2003086808\$-\$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/05/31 11:56
S24	2	("20030047785").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/05/31 11:56
S25	0	Garcia.in. and ("Zn.sub.2" near1 "Sn" near1 "O.sub.4")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/05/31 12:44
S26	0	("257"/\$7.ccls. "438"/\$7.ccls. "117"/\$7.ccls.) and ("Zn.sub.2" near1 "Sn" near1 "O.sub.4") near10 (semiconductor channel)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/31 12:45
S27	3	("257"/\$7.ccls. "438"/\$7.ccls. "117"/\$7.ccls.) and (zinc adj stannate "Zn.sub.2" near1 "Sn" near1 "O.sub.4") near10 (semiconductor channel)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/31 12:48
S28	10	(zinc adj stannate "Zn.sub.2" near1 "Sn" near1 "O.sub.4") near10 (semiconductor channel)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/31 12:49
S29	2	(zinc adj stannate "Zn.sub.2" near1 "Sn" near1 "O.sub.4") near10 (semiconductor channel) and (MOSFET MOS MISFET MESFET JFET NMOS NMOSFET PMOS PMOSFET field adj effect gate transistor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/31 12:50
S30	0	(zinc adj stannate "Zn.sub.2" near1 "Sn" near1 "O.sub.4") near10 (semiconductor channel) and (MOSFET MOS MISFET MESFET JFET NMOS NMOSFET PMOS PMOSFET field adj effect gate transistor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/05/31 13:02
S31	0	(zinc adj stannate "Zn.sub.2" near1 "Sn" near1 "O.sub.4" cubic adj spinel) near10 (semiconductor channel) and (MOSFET MOS MISFET MESFET JFET NMOS NMOSFET PMOS PMOSFET field adj effect gate transistor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/05/31 13:02

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S32	0	(zinc adj stannate "Zn.sub.2" near1 "Sn" near1 "O.sub.4" zinc adj spinel) near10 (semiconductor channel) and (MOSFET MOS MISFET MESFET JFET NMOS NMOSFET PMOS PMOSFET field adj effect gate transistor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/05/31 13:10
S33	324	transparent near1 (thin adj film adj transistor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/05/31 13:11
S34	0	(transparent near1 (thin adj film adj transistor tft) tft) and ("Zn.sub.2" near1 "Sn" near1 "O.sub.4")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/31 13:12
S35	0	((transparent near1 (thin adj film adj transistor tft)) tft) and ("Zn.sub.2" near1 "Sn" near1 "O.sub.4")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/31 13:12
S36	0	alumin\$1um adj titanate near6 gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/05/31 15:33
S37	9707	("AlO.sub."\$4 "TiO.sub."\$4 "Al.sub."\$4 alumin\$1um adj titanate titanium adj aluminate) and gate and (transistor field adj effect MOSFET MOS NMOS PMOS NMOSFET PMOSFET NMISFET PMISFET PMIS TFT thin adj film adj transistor OTFT)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 09:58
S38	115	((("TiO.sub."\$4 near4 "AlO.sub."\$4) (alumin\$1um adj titanate) (titanium adj aluminate)) and gate and (transistor field adj effect MOSFET MOS NMOS PMOS NMOSFET PMOSFET NMISFET PMISFET PMIS TFT thin adj film adj transistor OTFT)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 10:00
S39	79	((("TiO.sub."\$4 near4 "AlO.sub."\$4) (alumin\$1um adj titanate) (titanium adj aluminate)) and gate and (transistor field adj effect MOSFET MOS NMOS PMOS NMOSFET PMOSFET NMISFET PMISFET PMIS TFT thin adj film adj transistor OTFT) and @ad<"20030726"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 10:03

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S40	0	((("TiO.sub."\$4 near4 "AlO.sub."\$4) (alumin\$1um adj titanate) (titanium adj aluminate)) near15 gate and (transistor field adj effect MOSFET MOS NMOS PMOS NMOSFET PMOSFET NMISFET PMISFET PMIS TFT thin adj film adj transistor OTFT) and @ad<"20030726"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/02 10:16
S41	4	"763353".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/06/01 11:39
S42	706	((alumin\$1um adj oxide) ("Al.sub. "\$3 near1 (O "O.sub."\$3)) "AlO.sub. "\$3) near8 (titanium adj oxide ("Ti. sub."\$3 near1 (O "O.sub."\$3)) "TiO. sub."\$3) same gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 11:52
S43	131	((alumin\$1um adj oxide) ("Al.sub. "\$3 near1 (O "O.sub."\$3)) "AlO.sub. "\$3) near8 (titanium adj oxide ("Ti. sub."\$3 near1 (O "O.sub."\$3)) "TiO. sub."\$3) near10 gate near10 (dielectric insulati\$2)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 11:53
S44	66	((alumin\$1um adj oxide) ("Al.sub. "\$3 near1 (O "O.sub."\$3)) "AlO.sub. "\$3) near8 (titanium adj oxide ("Ti. sub."\$3 near1 (O "O.sub."\$3)) "TiO. sub."\$3) near10 gate near10 (dielectric insulati\$2)	USPAT	OR	ON	2006/06/01 11:53
S45	2	"20050253157".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/06/01 15:47
S46	140	rf adj sputtering near6 amorphous	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/06/01 15:47
S47	0	(zno zinc adj oxide) near10 (rf adj sputtering near6 amorphous)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 15:48
S48	16	(oxide) near10 (rf adj sputtering near6 amorphous)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 15:50

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S49	259	(oxide) near10 (sputtering near6 amorphous)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 15:50
S50	19	(zinc adj oxide zno) near10 (sputtering near6 amorphous)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 15:51
S51	1	(US-20050017244-\$.did.	US-PGPUB	OR	OFF	2006/06/01 16:10
S52	1	S51 and transparent	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 16:10
S53	0	dissocation adj constant near5 (zinc adj stannate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 16:17
S54	0	dissocation adj constant near5 ("Zn.sub.2" near1 "Sn" near1 "O. sub.4") (zinc adj stannate))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 16:40
S55	0	(indium-tin-oxide indium adj tin adj oxide ITO) and "20040127038".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 17:16
S56	11	drain-to-gate near4 bias	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 17:24
S57	1894	drain near2 connecti\$2 near2 gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 17:25
S58	7956	drain near1 connect\$3 near1 gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 17:25

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S59	571	drain near1 connecti\$3 near1 gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 17:33
S60	49	back adj gate and gate-to-drain	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 17:34
S61	2	back adj gate and gate-to-drain and (tft thin adj film adj transistor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 17:35
S62	2	back adj gate and gate-to-drain and (otft tft thin adj film adj transistor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 17:35
S63	2	(back adj gate back-gate) and gate-to-drain and (otft tft thin adj film adj transistor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 17:36
S64	334	(back adj gate back-gate) and (otft tft thin adj film adj transistor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 17:36
S65	267	(back adj gate back-gate) and (otft tft thin adj film adj transistor) and circuit	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 18:02
S66	29	hot adj electron.ti,ab,clm. and gate-to-drain	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 18:05
S67	585	hot adj electron.ti.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 18:11
S68	40	hot adj electron adj effect.ti.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 18:14

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S69	18	hot adj electron adj effect.ti. and gate near5 drain	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 18:15
S70	1	(US-20050017244-\$).did.	US-PGPUB	OR	OFF	2006/06/02 08:40
S71	0	S70 and means	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/06/02 08:41
S72	1	(US-20050017244-\$).did.	US-PGPUB	OR	OFF	2006/06/02 08:41
S73	0	S70 and "means"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/06/02 08:41
S74	524	(thin adj film adj transistor tft).ti,ab, clm. and (indium-tin ITO) near8 source and (indium-tin ITO) near8 drain	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/02 09:41
S75	54	(thin adj film adj transistor tft).ti,ab, clm. and (indium-tin ITO) near2 source and (indium-tin ITO) near2 drain	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/02 09:41

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S76	41	(US-20050104508-\$ or US-20040066484-\$ or US-20030185266-\$ or US-20050017244-\$ or US-20030207502-\$ or US-20030224550-\$ or US-20030219530-\$ or US-20030218222-\$ or US-20030218221-\$ or US-20030186489-\$ or US-20030139026-\$ or US-20030104659-\$ or US-20030180996-\$ or US-20030013261-\$ or US-20020171085-\$ or US-20020153587-\$ or US-20040127038-\$ or US-20040023432-\$ or US-20030047785-\$).did. or (US-4521698-\$ or US-6569720-\$ or US-6561174-\$ or US-6391462-\$ or US-6362499-\$ or US-5744864-\$ or US-5107314-\$ or US-4887255-\$ or US-4589026-\$ or US-5879973-\$ or US-5470768-\$ or US-6255655-\$ or US-6255130-\$ or US-4559238-\$ or US-6653206-\$ or US-6617609-\$ or US-7017830-\$).did. or (EP-40076-\$).did. or (JP-2003086808-\$).did. or (WO-200217368-\$ or WO-2004034449-\$ or US-20030047785-\$).did.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2006/06/02 10:16
S77	0	((("TiO.sub."\$4 near4 "AlO.sub."\$4) (alumin\$1um adj titanate) (titanium adj aluminate)) near15 gate and (transistor field adj effect MOSFET MOS NMOS PMOS NMOSFET PMOSFET NMISFET PMISFET PMIS TFT thin adj film adj transistor OTFT) and @ad<"20030726" and S76	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/02 10:17
S78	0	("AlO.sub."\$3 "A.sub.2O.sub.3") near10 ("TiO.sub."\$72 "TiO.sub.2") near10 ((insulati\$2 dielectric) near2 gate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/06/02 10:25
S79	69580	("Al.sub."\$1 near1 "O.sub."\$1)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/06/02 10:26

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S80	0	("Al.sub."\$1 near1 "O.sub."\$1) near20 ("Ti.sub."\$1 near1 "O.sub." \$1) near20 gate near20 (dielectric insulati\$2) near20 (combination multi-layer\$2 multilayer\$2)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/06/02 10:28
S81	0	("Al.sub."\$1 near1 "O.sub."\$1) near20 ("Ti.sub."\$1 near1 "O.sub." \$1) near20 gate near20 (dielectric insulati\$2)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/06/02 10:28
S82	87	((("Al.sub."\$1 near1 "O.sub."\$1) "AlO.sub."\$1) near20 (("Ti.sub."\$1 near1 "O.sub."\$1) "TiO.sub."\$1) near20 gate near20 (dielectric insulati\$2)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/06/02 10:30
S83	0	((("Al.sub."\$1 near1 "O.sub."\$1) "AlO.sub."\$1) near20 (("Ti.sub."\$1 near1 "O.sub."\$1) "TiO.sub."\$1) near20 gate near20 (dielectric insulati\$2) near20 mixture	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/06/02 10:30
S84	1	((("Al.sub."\$1 near1 "O.sub."\$1) "AlO.sub."\$1) near20 (("Ti.sub."\$1 near1 "O.sub."\$1) "TiO.sub."\$1) near20 gate near20 (dielectric insulati\$2) near20 mixture	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/02 10:35
S85	9	((("Al.sub."\$1 near1 "O.sub."\$1) "AlO.sub."\$1) near20 (("Ti.sub."\$1 near1 "O.sub."\$1) "TiO.sub."\$1) near20 gate near20 (dielectric insulati\$2) near20 (combination mixture multi-layer multi adj layer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/02 10:42
S86	0	((("Al.sub."\$1 near1 "O.sub."\$1) "AlO.sub."\$1) near20 (("Ti.sub."\$1 near1 "O.sub."\$1) "TiO.sub."\$1) near20 gate near20 (dielectric insulati\$2) near20 (combination mixture multi-layer multi adj layer) and (thin adj film adj transistor tft otft)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/02 10:43
S87	9	((("Al.sub."\$1 near1 "O.sub."\$1) "AlO.sub."\$1) near20 (("Ti.sub."\$1 near1 "O.sub."\$1) "TiO.sub."\$1) near20 gate near20 (dielectric insulati\$2) near20 (combination mixture multi-layer multi adj layer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/02 10:53

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S88	9	((("Al.sub."\$1 near1 "O.sub."\$1) "AlO.sub."\$1 (alumin\$1um adj titanate) (titanium adj aluminate)) near20 (("Ti.sub."\$1 near1 "O.sub. "\$1) "TiO.sub."\$1) near20 gate near20 (dielectric insulati\$2) near20 (combination mixture multi-layer multi adj layer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/02 10:55
S89	9	((("Al.sub."\$3 near1 "O.sub."\$3) "AlO.sub."\$3 (alumin\$1um adj titanate) (titanium adj aluminate)) near20 (("Ti.sub."\$3 near1 "O.sub. "\$3) "TiO.sub."\$3) near20 gate near20 (dielectric insulati\$2) near20 (combination mixture multi-layer multi adj layer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/02 12:48
S90	209	((("Al.sub."\$3 near1 "O.sub."\$3) "AlO.sub."\$3) near20 (("Ti.sub."\$3 near1 "O.sub."\$3) "TiO.sub."\$3) near20 barrier	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/02 12:49
S91	5	((("Al.sub."\$3 near1 "O.sub."\$3) "AlO.sub."\$3) near20 (("Ti.sub."\$3 near1 "O.sub."\$3) "TiO.sub."\$3) near20 barrier near20 gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/02 12:52
S92	0	((("Al.sub."\$3 near1 "O.sub."\$3) "AlO.sub."\$3) near20 (cap adj (layer film)) near20 gate near20 (semiconductor channel)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/02 12:53
S93	3	((alumin\$1um adj oxide) ("Al.sub. "\$3 near1 (O "O.sub."\$3)) "AlO.sub. "\$3) near8 (cap adj layer) near20 gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/02 12:59
S94	1839	((alumin\$1um adj oxide) ("Al.sub. "\$3 near1 (O "O.sub."\$3)) "AlO.sub. "\$3) near4 barrier	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/02 12:59
S95	45	((alumin\$1um adj oxide) ("Al.sub. "\$3 near1 (O "O.sub."\$3)) "AlO.sub. "\$3) near4 barrier near4 (Ti titanium)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/02 13:03
S96	27	((alumin\$1um adj oxide) ("Al.sub. "\$3 near1 (O "O.sub."\$3)) "AlO.sub. "\$3) near4 barrier near4 (Ti titanium) and gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/02 13:03

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S97	11320	((257/49) or (257/52) or (257/55) or (257/56) or (257/57) or (257/58) or (257/59) or (257/62) or (257/63) or (257/72) or (257/200) or (257/201) or (257/213) or (257/288) or (257/390) or (257/403) or (257/406) or (257/410) or (257/411)).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/06/02 14:32
S98	0	S97 and ((alumin\$1um adj titanate) (titanium adj aluminate) ("Al.sub.\$2 near1 "O.sub.\$2 "AlO.sub.\$2 alumin\$1um adj oxide)) near20 ("Ti.sub.\$2 near1 "O.sub.\$2 near1 "TiO.sub.\$2 (titanium adj oxide)) near20 gate and (channel semiconductor) near4 (("Zn.sub.\$2 near1 "SnO.sub.\$2) (("Zn.sub.\$2 near1 "O") near10 ("SnO.sub.\$2)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/02 14:47
S99	8	((("6836540") or ("6998656") or ("6940097") or ("7026713")).PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/06/02 14:49
S10 0	45	randy near1 hoffman.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/06/02 14:49
S10 1	26	randy near1 hoffman.in. and (zinc adj oxide ZnO ("Zn.sub.2" near1 "O")) and (Ti titanium) and (Al alumin\$1um)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/02 14:51
S10 2	89	(hewlett.as. hoffman.in. (hai near1 chiang).in. (john near2 wager).in.) and (zinc tin) adj oxide.ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/07/14 11:09
S10 3	2	(hewlett.as. hoffman.in. (hai near1 chiang).in. (john near2 wager).in.) and (zinc tin) adj oxide.ti,ab,clm. and stannate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/07/14 11:10
S10 4	18	(hewlett.as. hoffman.in. (hai near1 chiang).in. (john near2 wager).in.) and (zinc tin) adj oxide.ti,ab,clm. and (stannate "SnO.sub.\$2)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/07/14 11:10

EAST Search History

S10 5	2	"20040127038".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/07/14 12:05
S10 6	1	(US-20050017244-\$).did.	US-PGPUB	OR	OFF	2007/11/14 15:31
S10 7	0	(US-20050017244-\$).did. and means	US-PGPUB	OR	ON	2007/11/14 15:31
S10 8	1743	(aluminum adj oxide) and strontium adj oxide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/11/14 19:15
S10 9	7	"410830".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/11/15 10:27
S11 0	2	("20040127038").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/11/15 13:26
S11 1	0	("533453.ap.").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/11/15 14:15
S11 2	2	("20020172317").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/11/15 14:18
S11 3	2	("4093886").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/11/15 14:53
S11 4	0	wo-9108180\$-\$\$.did.	USPAT	OR	OFF	2007/11/15 14:54

EAST Search History

S11 5	2	wo-9108180\$-\$.did.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/11/15 16:23
S11 6	32	percentage near3 porosity near3 "%"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/11/15 16:24
S12 2	2	"20040127038".pn.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/11/21 10:03
S12 3	2	"4521698".PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/11/21 10:05
S12 4	2	"6674495".PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/11/21 10:05
S12 5	13	"6100558"	USPAT	OR	OFF	2007/11/21 10:50
S12 6	1	("6100558").PN.	USPAT; USOCR	OR	OFF	2007/11/21 10:52
S12 7	2	("20040169210").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/11/21 10:53

EAST Search History

S12 8	2	("6184946").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/11/21 10:53
S12 9	0	("20060183274").PN.	USPAT; USOCR	OR	OFF	2007/11/22 08:36
S13 0	9	carcia.in. and thin adj film adj transistor	US-PGPUB; USPAT	OR	ON	2007/11/22 08:44
S13 1	6	thin adj film adj transistor and (zinc-tin adj oxide zto) near4 channel	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/11/22 08:49
S13 2	7	(tft thin adj film adj transistor) and (zinc-tin adj oxide zto) near8 channel	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/11/22 08:50
S13 3	11	(tft thin adj film adj transistor) and (zinc-tin adj oxide zto zinc near1 tin near1 oxide) near8 channel	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/11/22 08:52
S13 4	12	(tft thin adj film adj transistor mos mosfet) and (zinc-tin adj oxide zto zinc near1 tin near1 oxide) near8 channel	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/11/22 08:53
S13 5	10	(mos mosfet) and (zinc-tin adj oxide zto zinc near1 tin near1 oxide) near8 channel	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/11/22 08:53

EAST Search History

S13 6	11	(mosfet transistor) and (zinc-tin adj oxide zto zinc near1 tin near1 oxide) near8 channel	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/11/22 08:56
S13 7	11	(mosfet transistor) and (zinc-tin adj oxide zto zinc near1 tin near1 oxide "zno:sn") near8 channel	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/11/22 09:03
S13 8	0	("20050017244").PN.	USPAT; USOCR	OR	OFF	2007/11/22 09:03
S13 9	2	("20050017244").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/11/22 09:06
S14 0	2	"20060284171"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/11/22 09:11
S14 1	10	zinc near1 tin near1 oxide near10 channel	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/11/22 09:12
S14 2	2	zinc near1 tin near1 oxide near10 channel not hoffman.in.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/11/22 09:32
S14 3	12023	zinc near2 tin near2 oxide zito zto "zno:sn" "sno"\$3"zn"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/11/22 09:33

EAST Search History

S14 4	26	(zinc near2 tin near2 oxide zito zto "zno:sn" "sno"\$3"zn") near4 channel	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/11/22 09:44
S14 5	0	zno near4 sno\$1 near4 (mixture combination) near10 channel and transistor	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/11/22 09:45
S14 6	0	zno near4 sno\$1 near8 (mixture combination) near10 channel and transistor	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/11/22 09:45
S14 7	5	(zinc adj oxide zno) near4 (tin adj oxide sno\$1) near8 (mixture combination) near10 channel and transistor	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/11/22 09:50
S14 8	31	(zinc adj oxide zno) near4 (tin adj oxide sno\$1) near10 channel and transistor	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/11/22 09:59
S14 9	1	(zinc-tin- adj oxide zinc adj tin adj oxide) near20 channel.clm.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/11/22 10:03
S15 0	2	"20040023432".pn.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/11/22 10:07

EAST Search History

S15 1	2	jp-2003088808\$-\$.did.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/11/22 10:10
S15 2	0	ohtomo.in. and zto	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/11/22 10:11
S15 3	0	ohtomo.in. and (zinc-tin-oxide zto)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/11/22 10:11
S15 4	0	(ohtomo.in. kawasaki.in.) and (zinc-tin-oxide zto)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/11/22 10:17
S15 5	23	"5470788"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/11/22 10:18
S15 6	3	((("5470788") or ("5879973") or ("6569720"))).PN.	USPAT; USOCR	OR	OFF	2007/11/22 10:24
S15 7	3	((("5470768") or ("5879973") or ("6569720"))).PN.	USPAT; USOCR	OR	OFF	2007/11/22 10:30
S15 8	11	((("4559238") or ("4589026") or ("4887255") or ("5107314") or ("5744864") or ("6255130") or ("6255655") or ("6362499") or ("6391462") or ("20020153587") or ("20020171085"))).PN.	US-PGPUB; USPAT	OR	OFF	2007/11/22 10:31

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S15 9	2	("20040127038").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/11/23 13:10
S16 0	13987	"SnO.sub.2"	USPAT	OR	OFF	2007/11/23 07:02
S16 1	0	"SnO.sub.2" near10 "ZnO" near10 (combination mixture) near20 channel and transistor	USPAT	OR	ON	2007/11/23 07:03
S16 2	4	"SnO.sub.2" near10 "ZnO" near10 (combination mixture) same channel and transistor	USPAT	OR	ON	2007/11/23 08:41
S16 3	2	jp-60198861\$-\$\$.did. /	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/11/23 08:41